



US 20220385246A1

(19) **United States**(12) **Patent Application Publication**
KAMIOKA et al.(10) **Pub. No.: US 2022/0385246 A1**(43) **Pub. Date: Dec. 1, 2022**(54) **HIGH-FREQUENCY AMPLIFIER, RADIO
COMMUNICATION DEVICE, AND RADAR
DEVICE**(52) **U.S. Cl.**
CPC **H03F 3/193** (2013.01); **H03F 2200/451**
(2013.01)(71) Applicant: **Mitsubishi Electric Corporation,**
Tokyo (JP)(72) Inventors: **Jun KAMIOKA,** Tokyo (JP); **Shintaro
SHINJO,** Tokyo (JP)(73) Assignee: **Mitsubishi Electric Corporation,**
Tokyo (JP)(21) Appl. No.: **17/882,105**(22) Filed: **Aug. 5, 2022****Related U.S. Application Data**(63) Continuation of application No. PCT/JP2020/
015343, filed on Apr. 3, 2020.**Publication Classification**(51) **Int. Cl.**
H03F 3/193 (2006.01)(57) **ABSTRACT**

A high-frequency amplifier includes: a common-source transistor that has gate fingers, drain fingers, and source fingers, amplifies a signal applied to each of the gate fingers as a signal to be amplified, and outputs an amplified signal from each of the drain fingers; a common-gate transistor that has source fingers connected to the drain fingers of the common-source transistor, drain fingers, and gate fingers, and amplifies the amplified signal output from each of the drain fingers of the common-source transistor; a gate bus bar connected to the gate fingers of the common-gate transistor; and capacitors each having a first end connected to the gate bus bar and a second end grounded: wherein the capacitors are arranged at respective positions where impedances obtained by looking toward the respective capacitors from the respective gate fingers of the common-gate transistor are equal to each other.

